Product data sheet

1. General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- · Fast switching
- Guaranteed ESD capability
- High thermal cycling performance
- Low on-state loss
- Low thermal resistance
- Rugged: reverse voltage surge capability
- Soft recovery minimizes power-consuming oscillations

3. Applications

Output rectifiers in high-frequency switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage			-	-	200	V
I _{F(AV)}	average forward current	SQW; $\delta = 0.5$; $T_{mb} \le 128$ °C; <u>Fig. 1</u> ; <u>Fig. 2</u>		-	-	8	Α
Static characte	eristics						,
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>		-	0.8	0.895	V
Dynamic chara	acteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/s}$; $T_j = 25 \text{ °C}$; ramp recovery; Fig. 5; Fig. 7		-	20	25	ns
Electrostatic discharge							
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ		-	-	8	kV





Ultrafast power diode

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode	}	001aaa020
mb	mb	mounting base; cathode	TO-220AC (SOD59)	

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
BYW29E-200	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59				

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	200	V
V_{RWM}	crest working reverse voltage		-	200	V
V_R	reverse voltage		-	200	V
I _{F(AV)}	average forward current	SQW; δ = 0.5 ; T _{mb} ≤ 128 °C; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	8	А
I _{FRM}	repetitive peak forward current	SQW; δ = 0.5 ; t_p = 25 μ s; $T_{mb} \le$ 128 °C	-	16	Α
I _{FSM}	non-repetitive peak forward	SIN; $t_p = 8.3 \text{ ms}$; $T_{j(init)} = 25 \text{ °C}$	-	88	Α
	current	SIN; t_p = 10 ms; $T_{j(init)}$ = 25 °C	-	80	Α
I _{RRM}	repetitive peak reverse current	$\delta = 0.001$; $t_p = 2 \mu s$	-	0.2	Α
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs	-	0.2	Α
T _{stg}	storage temperature		-40	150	°C

BYW29E-200

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Ultrafast power diode

Symbol	Parameter	Conditions		Min	Max	Unit	
T _j	junction temperature			-	150	°C	
Electrostatic d	Electrostatic discharge						
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ		-	8	kV	

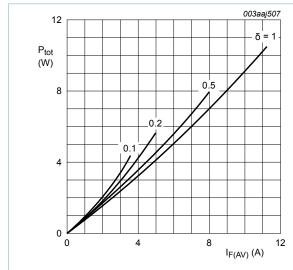


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_{O} &= 0.791 \text{ V; } R_{S} = 0.013 \text{ } \Omega \end{split}$$

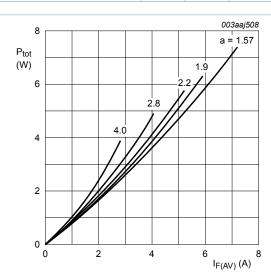


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

$$\begin{aligned} \mathbf{a} &= \mathbf{form} \ \mathbf{factor} = I_{F(RMS)} / I_{F(AV)} \\ \mathbf{V}_{\mathrm{O}} &= \mathbf{0.791} \ \mathbf{V}; \ \mathbf{R}_{\mathrm{S}} = \mathbf{0.013} \ \Omega \end{aligned}$$

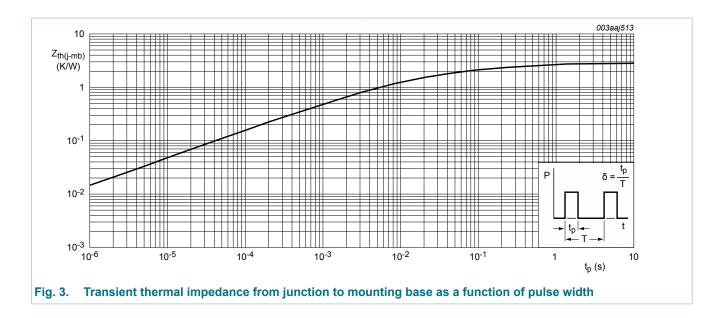
8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 3	-	-	2.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

3/10

Ultrafast power diode

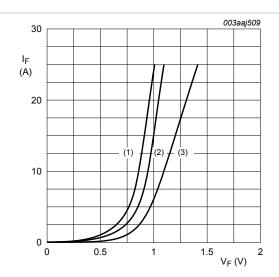


9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	M	lin	Тур	Max	Unit
Static char	acteristics					'	,
V_{F}	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 4</u>	-		0.92	1.05	V
		I _F = 20 A; T _j = 25 °C; <u>Fig. 4</u>	-		1.1	1.3	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 4</u>	-		8.0	0.895	V
I _R	reverse current	V _R = 200 V; T _j = 25 °C	-		2	10	μA
		V _R = 200 V; T _j = 100 °C	-		0.2	0.6	mA
Dynamic cl	haracteristics						
Q _r	recovered charge	I _F = 2 A; V _R = 30 V; dI _F /dt = 20 A/s; T _j = 25 °C; <u>Fig. 5</u> ; <u>Fig. 6</u>	-		4	11	nC
t _{rr} ro	reverse recovery time	$I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 100 \text{ A/s;}$ $T_j = 25 \text{ °C; } ramp \text{ recovery; } Fig. 5; Fig. 7$	-		20	25	ns
		$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{R(meas)} = 0.25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ step recovery}; Fig. 8$	-		15	20	ns
V_{FRM}	forward recovery voltage	$I_F = 1 \text{ A}; dI_F/dt = 10 \text{ A/s}; T_j = 25 ^{\circ}\text{C};$ Fig. 9	-		1	-	V

Ultrafast power diode





(1) $T_i = 150$ °C; typical values;

(2) T_i = 150 °C; maximum values;

(3) $T_i = 25$ °C; maximum values;

 $V_O = 0.791 \text{ V}; R_S = 0.013 \Omega$

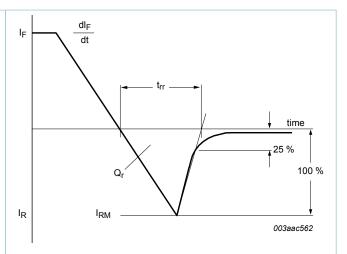


Fig. 5. Reverse recovery definitions; ramp recovery

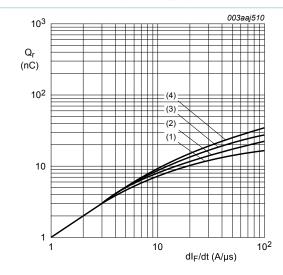


Fig. 6. Recovered charge as a function of rate of change of forward current; maximum values

(1)
$$I_F = 1 A$$
; $T_i = 25 \, ^{\circ}\text{C}$

(2)
$$I_F = 2 A$$
; $T_j = 25 \, ^{\circ}\mathrm{C}$

(3)
$$I_F = 5 A$$
; $T_j = 25 \, ^{\circ}\text{C}$

(4)
$$I_F = 10 A$$
; $T_i = 25 °C$

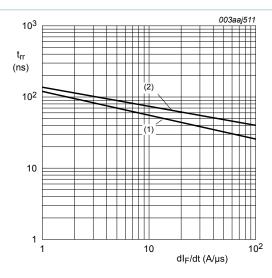
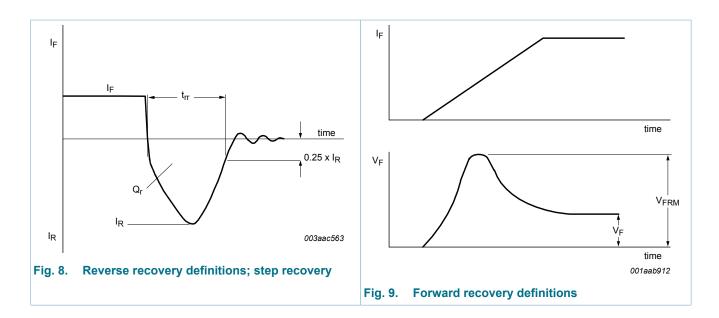


Fig. 7. Reverse recovery time as a function of rate of change of forward current; maximum values

(1)
$$I_F = 1 A$$
; $T_i = 25 \, ^{\circ}C$

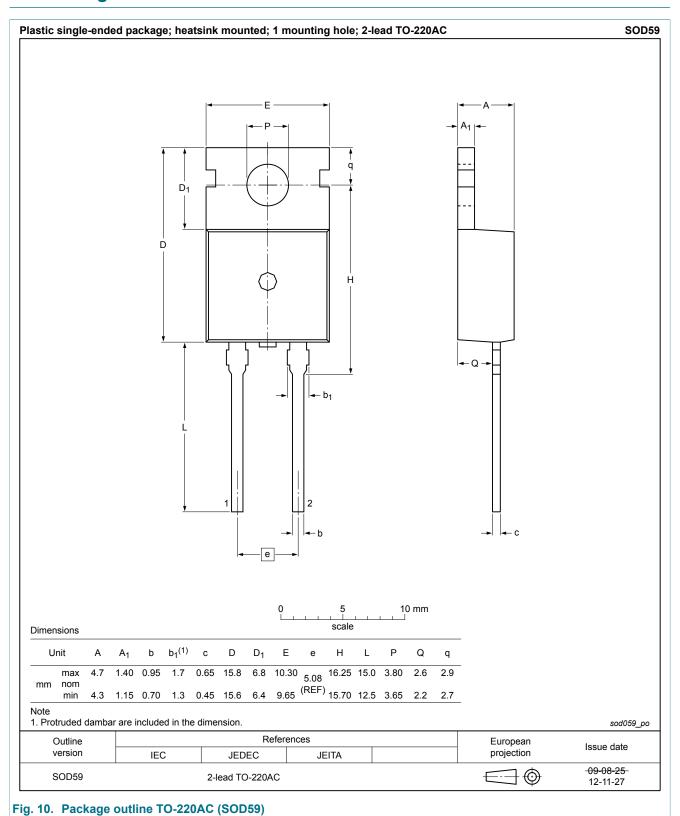
(2)
$$I_F = 10 \text{ A}; T_j = 25 \text{ }^{\circ}\text{C}$$

Ultrafast power diode



Ultrafast power diode

10. Package outline



7/10

Ultrafast power diode

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11.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Ultrafast power diode

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Ultrafast power diode

12. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Limiting values	2
8	Thermal characteristics	3
9	Characteristics	4
10	Package outline	7
11	Legal information	
11.1	Data sheet status	8
11.2	Definitions	8
11.3	Disclaimers	8
11.4	Trademarks	9

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